This can be obtained by taking the ratio of the concentration of the activity in the front 5% of the ingot, to that of the impurity originally added, and gives an indication of the purification obtained under conditions in which volatilization is occurring. These ratios, which we have described as purification factors, are also given in Table I. Although they are clearly dependent on the conditions of the experiment, they do give an indication of the behavior of these impurities that could be expected on zone refining aluminum antimonide.

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Any discussion of this paper will appear in a Discussion Section to be published in the December 1960 Journal.

REFERENCE


Corrections

In the discussion of the paper by P. E. Lake and E. J. Casey, "The Anodic Oxidation of Cadmium, I. Mechanism of Film Formation," which appeared in the June 1959 Journal, in column 1 on page 533 it should read $R_x = \frac{I_t}{t + \tau}$ rather than $R_x = \frac{I_t}{\tau}$.

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In the paper by B. Schwartz, "The Use of Organo-Substituted Hydrolyzable Silanes on Silicon Devices," which appeared in the October 1959 Journal, the following corrections should be made:

Page 871, column 1, paragraph 2, line 4—"... while $R$ is an organic..." should read "... where $R$ is an organic..."

Page 871, column 2, paragraph 1, line 5—"... this technique is the one preferred to..." should read "... this technique is the one referred to..."

Page 872, Table I, column 6, and Table III, column 1—"$I_x, \mu a$" should read "$I_x, \mu a$"

Page 873, column 2, paragraph 3, line 3—"creating a silicon coating on the surface..." should read "... creating a silicone coating on the surface..."

Page 873, Reference 3—"General Electric Rev." should read "General Electric Rev."